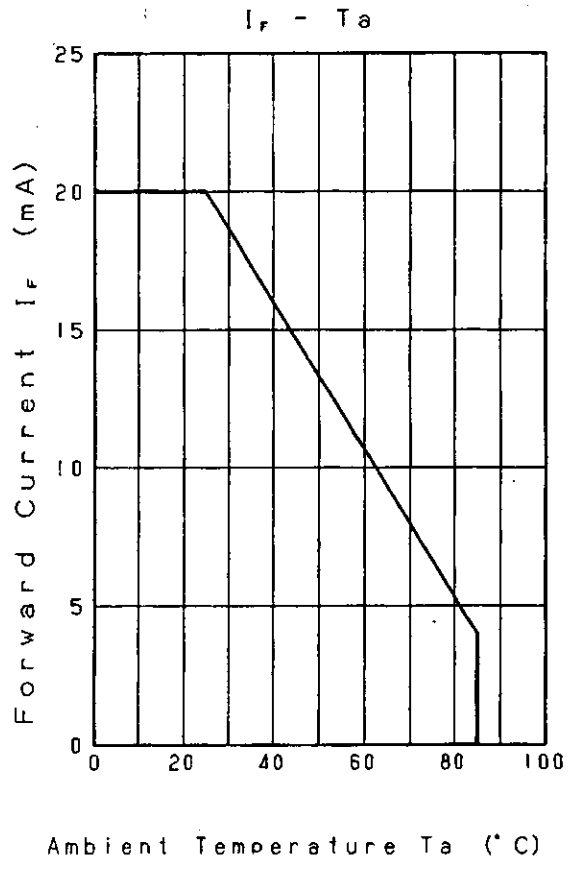
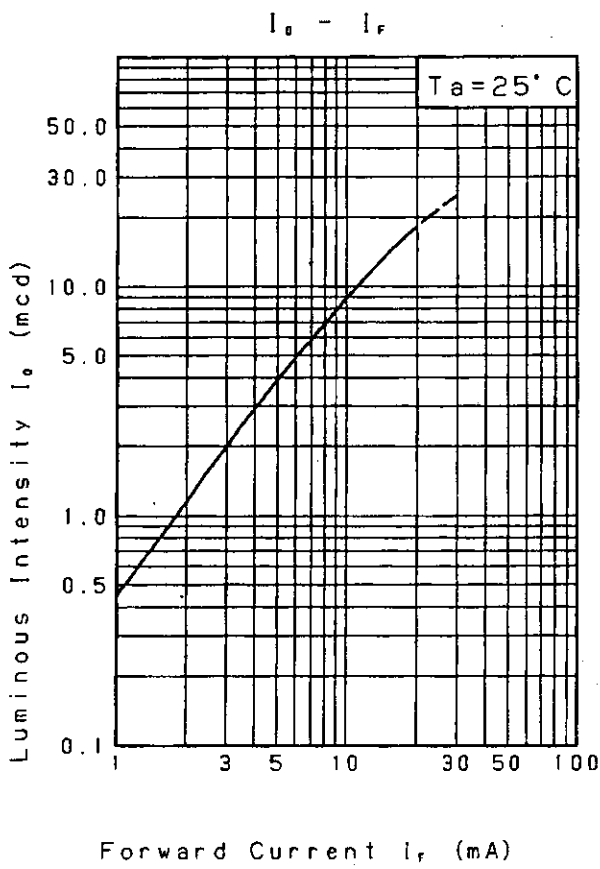
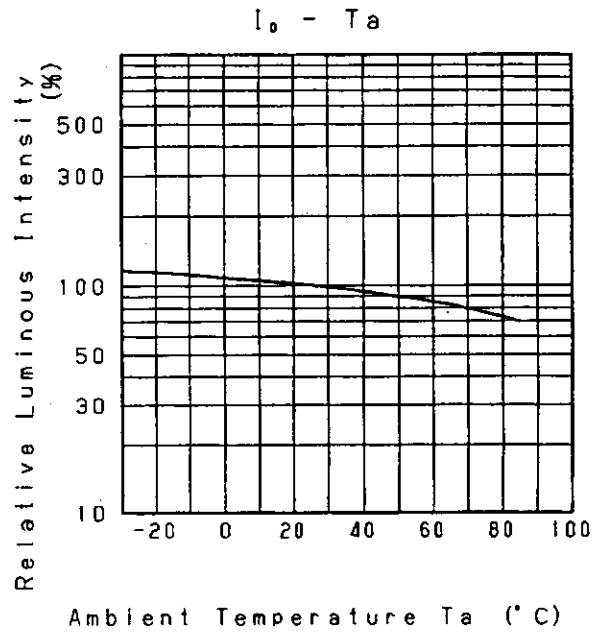
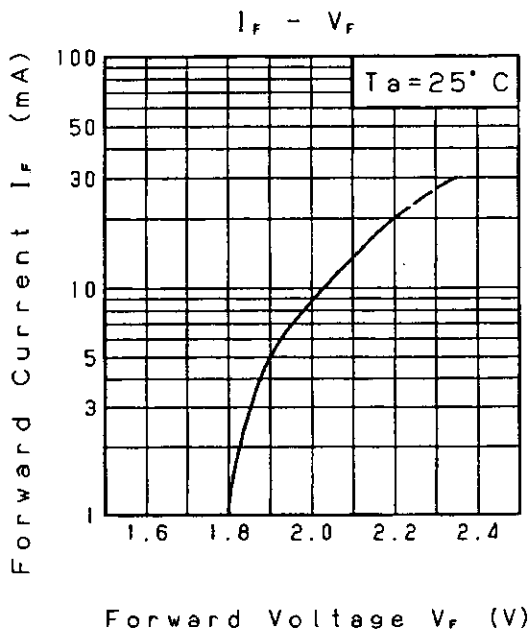


Approved	Checked	Designed	DEVELOPMENT SPECIFICATION							
T. Shoda	M. Mori	T. Tabata	P/N: LNJ316C8TRA							
T	Y	P	E	Green Light Emitting Diode						
APPLICATION			Indicators							
MATERIAL			GaP							
OUTLINE			Attached							
ABSOLUTE MAXIMUM RATINGS			P	*I _{FP}	I _{FDC}	V _R	Topr	Tstg		
			60	100	20	4	-30~+85	-40~+100		
			mW	mA	mA	V	°C	°C		
CONDITION			T _a = 25 ± 3°C							
Test Specification										
I t e m	Symbol	C o n d i t i o n	Typ	Limit		Unit				
				Min	Max					
Forward Voltage	V _F	I _F = 10 mA	2.03		2.6	V				
Reverse Leakage Current	I _R	V _R = 4 V			10	μA				
Luminous Intensity	I _O	I _F = 10 mA DC	8.8	3.3		mcđ				
Peak Emission Wavelength	λ _p	I _F = 10 mA DC	565			nm				
Spectral Line Half Width	Δλ	I _F = 10 mA DC	30			nm				
<p>* · The Condition of I_{FP} is duty 10 % , Pulse width 1 ms</p> <p>· Please contact the Panasonic local office if you design at low current (below 1 mA DC) or pulse current operation and have any questions.</p>										
<p>NOTE</p> <p>★1. Soldering conditions. Refer to Handling note.</p> <p>★2. Care should be taken that soldering is done within 3-days after opening the dry package and reel.</p> <p>★3. Compositions of the lead ····· Cu/Ni/Au plating</p>										
Apr. 6. 1999										

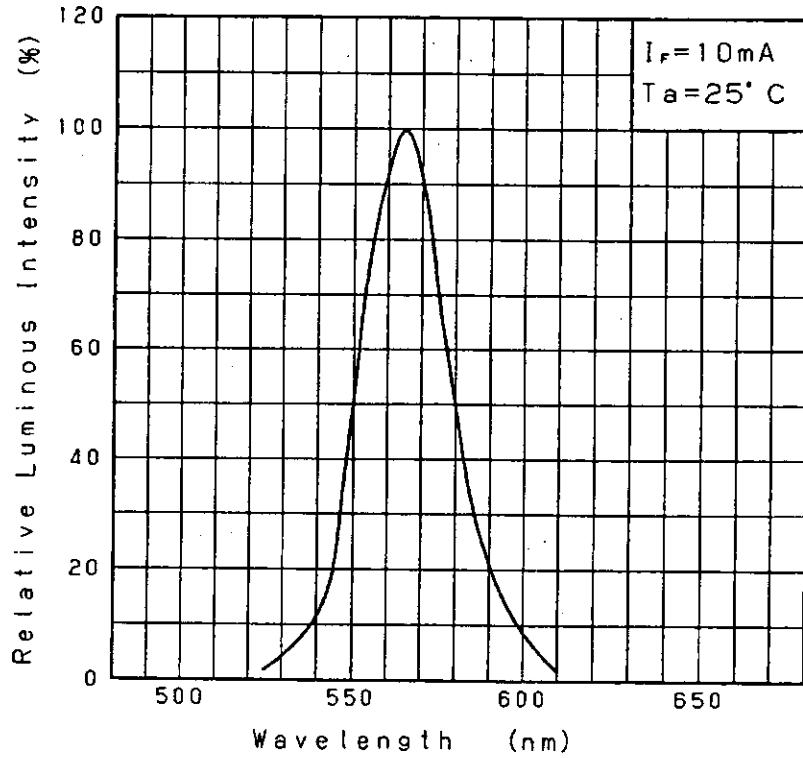
Approved	Checked	Designed	DEVELOPMENT SPECIFICATION			
T. Akeda	M. Ichi	T. Tabata		P/N: LNJ316C8TRA		



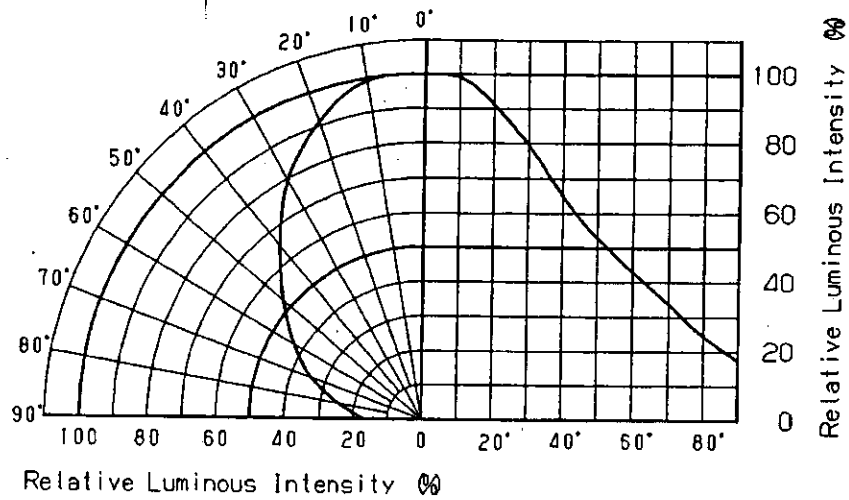
Apr. 6. 1999			

Approved	Checked	Designed	DEVELOPMENT SPECIFICATION			
T. Shudo	M. Ni	T. Taketa	P/N: LN316C8TRA			

Relative Luminous Intensity
Wavelength Characteristics

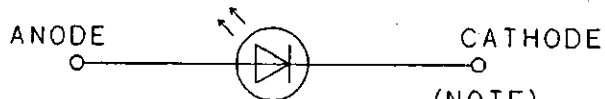
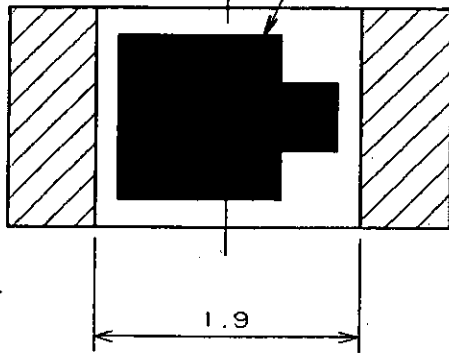
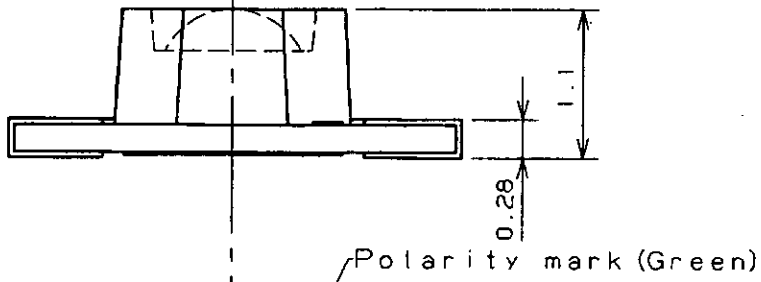
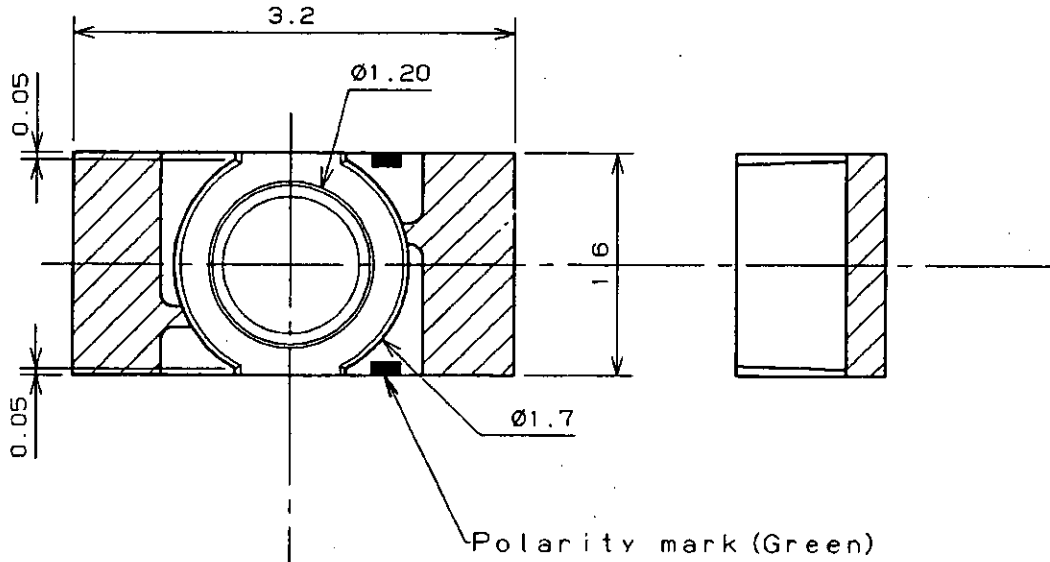


Directive Characteristics



Apr. 6. 1999			
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Approved	Checked	Designed	DEVELOPMENT SPECIFICATION (OUTLINE) P/N: LNJ316C8TRA		
<i>T. Shirota</i>	<i>M. Imai</i>	<i>T. Tabata</i>			



(NOTE)
 1. Unit: mm
 2. Tolerance unless specified is ± 0.15 .
 3. indicate Au terminal.

Nov. 12. 1999			